

Product Overview

MBR120VLSF: 1.0 A, 20 V, Schottky Power Rectifier, Surface Mount

For complete documentation, see the data sheet.

The MBR120VLSFT1 uses the Schottky Barrier principle with a large area metal-to-silicon power diode. Ideally suited for low voltage, high frequency rectification or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system. This package also provides an easy to work with alternative to the leadless 34 package style. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are ac/dc and dc/dc converters, reverse battery protection, "ORing" of multiple supply voltages and any other application where performance and size are critical.

Features

- Guardring for Stress Protection
- Optimized for Very Low Forward Voltage
- 125 C Operating Junction Temperature
- Epoxy Meets UL94, VO
- Package Designed for Optimal Automated Board Assembly
- ESD Rated Machine Model C
- ESD Rated Human Body Model 3B
- Device Meets MSL 1 Requirements
- Pb-Free Packages are Available

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Configuration	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (μ A)	$I_{O(rec)Max}$ (A)	I_{FSM} Max (A)	t_{rr} Max (ns)	C_j Max (pF)	Package Type
MBR120VLSFT1G	0.0769	Pb-free	Active	Single	20	0.34	600	1	45	-	-	SOD-123FL
		Halide free non AEC-Q and PPAP										
MBR120VLSFT3G	0.0885	Pb-free	Active	Single	20	0.34	600	1	45	-	-	SOD-123FL
		Halide free non AEC-Q and PPAP										
NRVB120VLSFT1G	0.1243	AEC Qualified PPAP Capable Pb-free Halide free	Active	Single	20	0.34	600	1	45	-	-	SOD-123FL

For more information please contact your local sales support at www.onsemi.com.

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